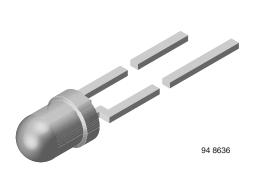
HALOGEN FREE

GREEN



Vishay Semiconductors

Infrared Emitting Diode, 950 nm, GaAs



DESCRIPTION

TSUS4400 is an infrared, 950 nm emitting diode in GaAs technology molded in a blue tinted plastic package.

FEATURES

Package type: leadedPackage form: T-1

Dimensions (in mm): Ø 3

• Peak wavelength: $\lambda_p = 950 \text{ nm}$

High reliability

• Angle of half intensity: $\varphi = \pm 18^{\circ}$

• Low forward voltage

• Suitable for high pulse current operation

• Good spectral matching with Si photodetectors

 Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



- Infrared remote control and free air transmission systems with low forward voltage and small package requirements
- Emitter in transmissive sensors
- · Emitter in reflective sensors

| PRODUCT SUMMARY | | | | | |
|-----------------|------------------------|---------|---------------------|---------------------|--|
| COMPONENT | I _e (mW/sr) | φ (deg) | λ _p (nm) | t _r (ns) | |
| TSUS4400 | 15 | ± 18 | 950 | 800 | |

Note

• Test conditions see table "Basic Characteristics"

| ORDERING INFORMATION | | | | |
|----------------------|-----------|------------------------------|--------------|--|
| ORDERING CODE | PACKAGING | REMARKS | PACKAGE FORM | |
| TSUS4400 | Bulk | MOQ: 5000 pcs, 5000 pcs/bulk | T-1 | |

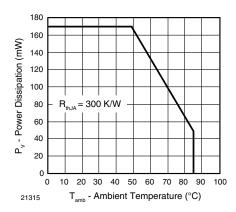
Note

MOQ: minimum order quantity

| PARAMETER | FINGS (T _{amb} = 25 °C, unless otherwise TEST CONDITION | SYMBOL | VALUE | UNIT |
|-------------------------------------|---|-------------------|-------------|------|
| Reverse voltage | 1201 CONZINON | V _R | 5 | V |
| Forward current | | I _F | 100 | mA |
| Peak forward current | $t_p/T = 0.5, t_p = 100 \mu s$ | I _{FM} | 200 | mA |
| Surge forward current | t _p = 100 μs | I _{FSM} | 2 | А |
| Power dissipation | | P _V | 170 | mW |
| Junction temperature | | Tj | 100 | °C |
| Operating temperature range | | T _{amb} | -40 to + 85 | °C |
| Storage temperature range | | T _{stg} | -40 to +100 | °C |
| Soldering temperature | t ≤ 5 s, 2 mm from case | T _{sd} | 260 | °C |
| Thermal resistance junction/ambient | J-STD-051, leads 7 mm, soldered on PCB | R _{thJA} | 300 | K/W |



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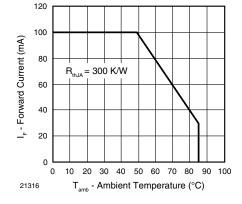


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

Fig. 2 - Forward Current Limit vs. Ambient Temperature

| BASIC CHARACTERISTICS (T _{amb} = 25 °C, unless otherwise specified) | | | | | | |
|---|---|-------------------|------|------|------|-------|
| PARAMETER | TEST CONDITION | SYMBOL | MIN. | TYP. | MAX. | UNIT |
| Forward voltage | $I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$ | V _F | | 1.3 | 1.7 | V |
| | $I_F = 1.5 \text{ A}, t_p = 100 \mu \text{s}$ | V _F | | 2.2 | | V |
| Temperature coefficient of V _F | I _F = 100 mA | TK _{VF} | | -1.3 | | mV/K |
| Reverse current | V _R = 5 V | I _R | | | 100 | μΑ |
| Breakdown voltage | I _R = 100 μA | V _(BR) | 5 | 40 | | μΑ |
| Junction capacitance | $V_R = 0 \text{ V, } f = 1 \text{ MHz, } E = 0$ | Cj | | 30 | | pF |
| Dadient intensity | $I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$ | l _e | 7 | 15 | 35 | mW/sr |
| Radiant intensity | $I_F = 1.5 \text{ A}, t_p = 100 \mu \text{s}$ | l _e | | 140 | | mW/sr |
| Radiant power | $I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$ | фe | | 20 | | mW |
| Temperature coefficient of ϕ_e | I _F = 20 mA | TKφ _e | | -0.8 | | %/K |
| Angle of half intensity | | φ | | ± 18 | | deg |
| Peak wavelength | I _F = 100 mA | λρ | | 950 | | nm |
| Spectral bandwidth | I _F = 100 mA | Δλ | | 50 | | nm |
| Temperature coefficient of λ_p | I _F = 100 mA | TKλ _p | | 0.2 | | nm/K |
| Rise time | I _F = 100 mA | t _r | | 800 | | ns |
| | I _F = 1.5 A | t _r | | 400 | | ns |
| Fall time | I _F = 100 mA | t _f | | 800 | | ns |
| | I _F = 1.5 A | t _f | | 400 | | ns |
| Virtual source diameter | | d | | 2.1 | | mm |

BASIC CHARACTERISTICS (T_{amb} = 25 °C, unless otherwise specified)

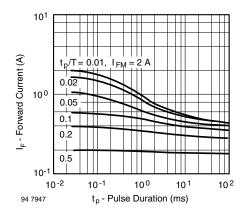


Fig. 3 - Pulse Forward Current vs. Pulse Duration

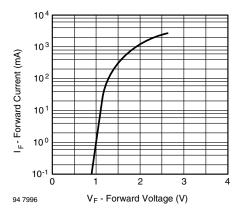


Fig. 4 - Forward Current vs. Forward Voltage

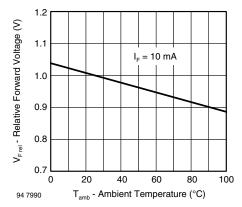


Fig. 5 - Relative Forward Voltage vs. Ambient Temperature

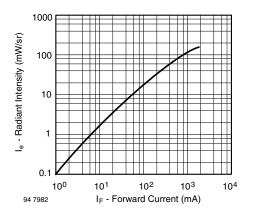


Fig. 6 - Radiant Intensity vs. Forward Current

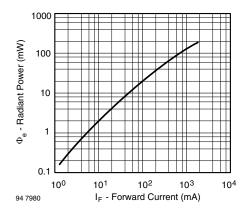


Fig. 7 - Radiant Power vs. Forward Current

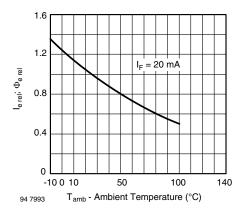
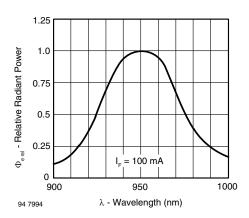


Fig. 8 - Relative Radiant Intensity/Power vs. Ambient Temperature



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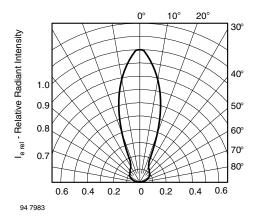
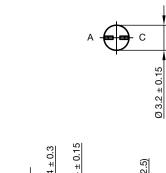
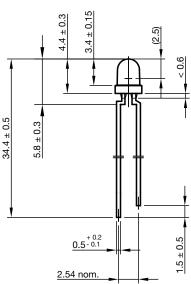
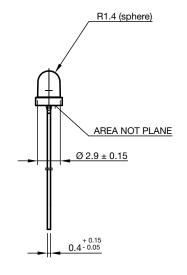


Fig. 10 - Relative Radiant Intensity vs. Angular Displacement

PACKAGE DIMENSIONS in millimeters







technical drawings according to DIN specifications

Drawing-No.: 6.544-5255.01-4

Issue: 9; 28.07.14



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